

BUK9K134-100E

Dual N-channel 100 V, 159 m Ω logic level MOSFET

10 December 2013

Product data sheet

1. General description

Dual logic level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Dual MOSFET
- Q101 Compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{GS(th)} rating of greater than 0.5 V at 175 °C

3. Applications

- 12 V, 24 V and 48 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|---------------------------------------|----------------------------------|--|--|-----|-----|-----|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | - | 100 | V |
| I _D | drain current | V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 1</u> | | - | - | 8.5 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 2</u> | | - | - | 32 | W |
| Static characteristics FET1 and FET2 | | | | | | | |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$ | | - | 127 | 159 | mΩ |
| Dynamic characteristics FET1 and FET2 | | | | | | | |
| Q_{GD} | gate-drain charge | $I_D = 5 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 5 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$ | | - | 3.6 | - | nC |



5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|---|----------------|
| 1 | S1 | source1 | 8 7 6 5 | D1 D1 D2 D2 |
| 2 | G1 | gate1 | \ | |
| 3 | S2 | source2 | | |
| 4 | G2 | gate2 | | |
| 5 | D2 | drain2 | | |
| 6 | D2 | drain2 | | mbk725 |
| 7 | D1 | drain1 | 1 2 3 4 LFPAK56D (SOT1205) | |
| 8 | D1 | drain1 | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | | |
|---------------|----------|--|---------|--|--|--|
| | Name | Description | Version | | | |
| BUK9K134-100E | LFPAK56D | Plastic single ended surface mounted package (LFPAK56D); 8 leads | SOT1205 | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|---------------|--------------|
| BUK9K134-100E | 913410E |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|-----------------|----------------------|--|--------|-----|-----|------|
| V_{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | 100 | V |
| V_{DGR} | drain-gate voltage | R_{GS} = 20 k Ω | | - | 100 | V |
| V_{GS} | gate-source voltage | T _j ≤ 175 °C; DC | | -10 | 10 | V |
| | | T _j ≤ 175 °C; Pulsed | [1][2] | -15 | 15 | V |
| I _D | drain current | T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 1</u> | | - | 8.5 | Α |
| | | T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 1</u> | | - | 6 | Α |
| I _{DM} | peak drain current | T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 4 | | - | 34 | Α |

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| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|--|---|--------|-----|------|------|
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 2</u> | | - | 32 | W |
| T _{stg} | storage temperature | | | -55 | 175 | °C |
| T _j | junction temperature | | | -55 | 175 | °C |
| Source-drai | in diode FET1 and FET2 | ' | | | | |
| Is | source current | T _{mb} = 25 °C | | - | 8.5 | Α |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | | - | 34 | Α |
| Avalanche I | Ruggedness FET1 and FET2 | | | | ' | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | I_D = 8.5 A; $V_{sup} \le 100 \text{ V}$; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; Fig. 3 | [3][4] | - | 12.6 | mJ |

- [1] Accumulated Pulse duration up to 50 hours delivers zero defect ppm
- [2] Significantly longer life times are achieved by lowering T_i and or V_{GS}.
- [3] Refer to application note AN10273 for further information
- [4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

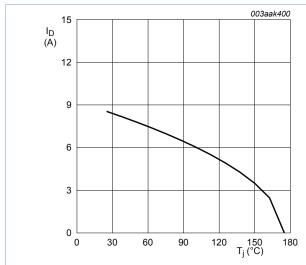


Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 5V$$

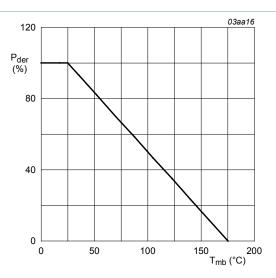


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

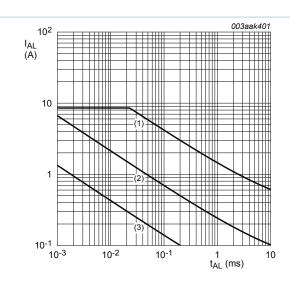
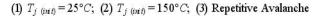


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time



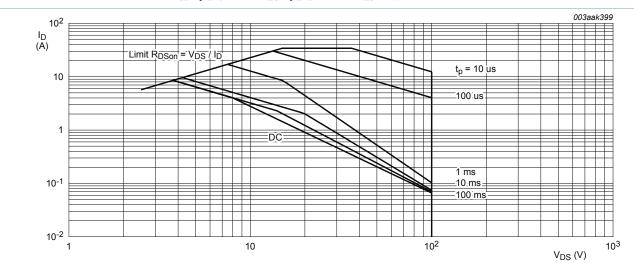


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

9. Thermal characteristics

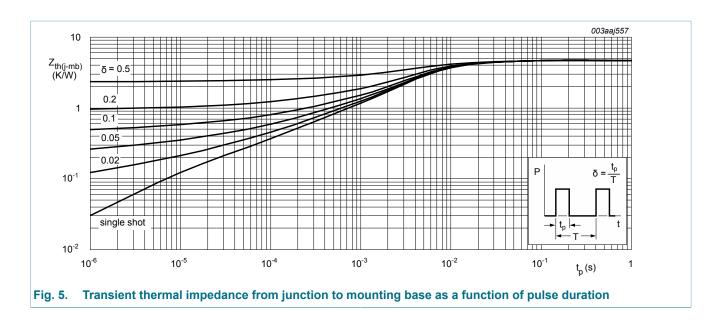
Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---|---|-----|-----|------|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | Fig. 5 | - | - | 4.68 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | Minimum footprint; mounted on a printed circuit board | - | 95 | - | K/W |

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10. Characteristics

Table 7. Characteristics

| drain-source breakdown voltage gate-source threshold voltage | $I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$ $I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ $I_D = 1 \ mA; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C;$ Fig. 9; Fig. 10 | 90 100 1.4 | - - 1.7 | - | V |
|---|---|---|---------------|------|----|
| breakdown voltage gate-source threshold | I_D = 250 μ A; V_{GS} = 0 V; T_j = 25 °C I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10 | 100 | - | - | |
| gate-source threshold | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 9; Fig. 10 | | | | V |
| _ | Fig. 9; Fig. 10 | 1.4 | 1.7 | 2.4 | _ |
| | 1 4 A . V T 475 00 | | | 2.1 | V |
| | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9; Fig. 10 | 0.5 | - | - | V |
| | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; Fig. 9; Fig. 10 | - | - | 2.45 | V |
| drain leakage current | V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C | - | 0.02 | 1 | μΑ |
| | V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C | - | - | 500 | μA |
| gate leakage current | V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C | - | 2 | 100 | nA |
| | V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C | - | 2 | 100 | nA |
| drain-source on-state | V _{GS} = 5 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u> | - | 127 | 159 | mΩ |
| resistance | V _{GS} = 5 V; I _D = 5 A; T _j = 175 °C; Fig. 11; Fig. 12 | - | 351 | 439 | mΩ |
| | V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u> | - | 122 | 154 | mΩ |
| cteristics FET1 and FE | T2 | I | | | |
| total gate charge | I _D = 5 A; V _{DS} = 80 V; V _{GS} = 5 V; | - | 7.4 | - | nC |
| gate-source charge | T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u> | - | 1.4 | - | nC |
| gate-drain charge | | - | 3.6 | - | nC |
| | resistance cteristics FET1 and FE total gate charge gate-source charge | drain-source on-state resistance $V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; \underline{\text{Fig. 11}}$ $V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; T_j = 175 \text{ °C};$ $\underline{\text{Fig. 11}}; \underline{\text{Fig. 12}}$ $V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; \underline{\text{Fig. 11}}$ $\underline{\text{Cteristics FET1 and FET2}}$ $\underline{\text{total gate charge}}$ $\underline{\text{gate-source charge}}$ $\underline{\text{gate-drain charge}}$ | | | |

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|----------------------------------|------------------------------|---|--|-----|------|-----|------|
| C _{iss} | input capacitance | V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; | | - | 566 | 755 | pF |
| C _{oss} | output capacitance | T _j = 25 °C; <u>Fig. 15</u> | | - | 55 | 66 | pF |
| C _{rss} | reverse transfer capacitance | | | - | 38 | 53 | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 80 V; R_{L} = 16 Ω ; V_{GS} = 5 V; $R_{G(ext)}$ = 5 Ω ; I_{D} = 5 A; T_{j} = 25 °C | | - | 6.2 | - | ns |
| t _r | rise time | | | - | 11.3 | - | ns |
| t _{d(off)} | turn-off delay time | | | - | 12 | - | ns |
| t _f | fall time | | | - | 10.3 | - | ns |
| Source-drain diode FET1 and FET2 | | | | | | | |
| V_{SD} | source-drain voltage | $I_S = 5 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 16$ | | - | 0.83 | 1.2 | V |
| t _{rr} | reverse recovery time | $I_S = 5 \text{ A}; \text{ d}I_S/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ $\text{V}_{DS} = 50 \text{ V}; \text{ T}_j = 25 ^{\circ}\text{C}$ | | - | 32.3 | - | ns |
| Q _r | recovered charge | | | - | 39.9 | - | nC |

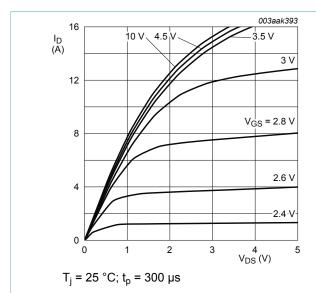


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

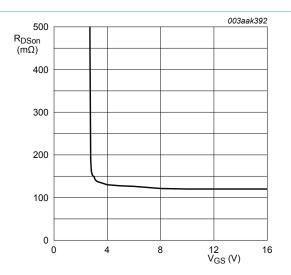


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25$$
°C; $I_D = 5A$

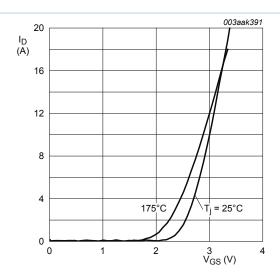


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



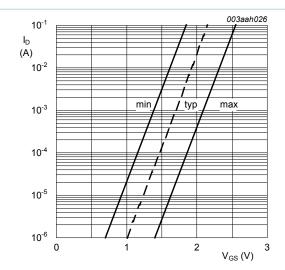


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25$$
°C; $V_{DS} = 5V$

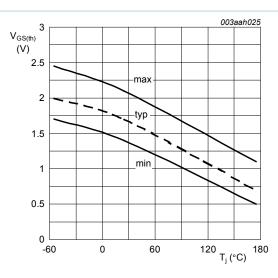
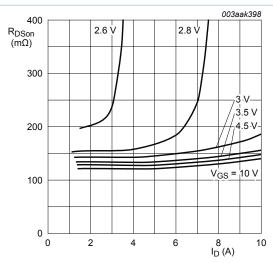


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1$$
 mA; $V_{DS} = V_{GS}$



 $T_i = 25 \,^{\circ}\text{C}; t_p = 300 \,\mu\text{s}$

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

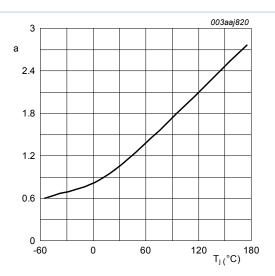


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

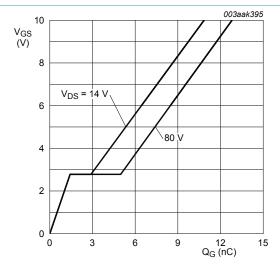


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25$$
°C; $I_D = 5A$

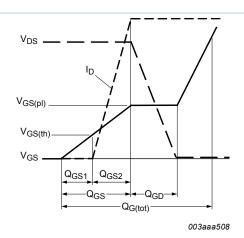


Fig. 13. Gate charge waveform definitions

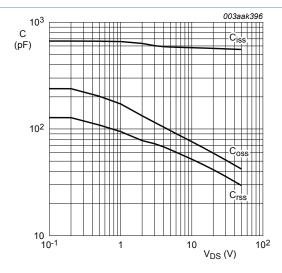


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; f = \mathbf{1}MHz$$

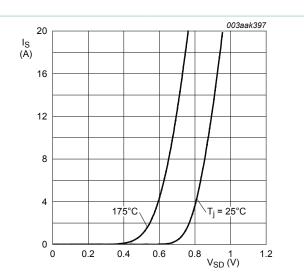
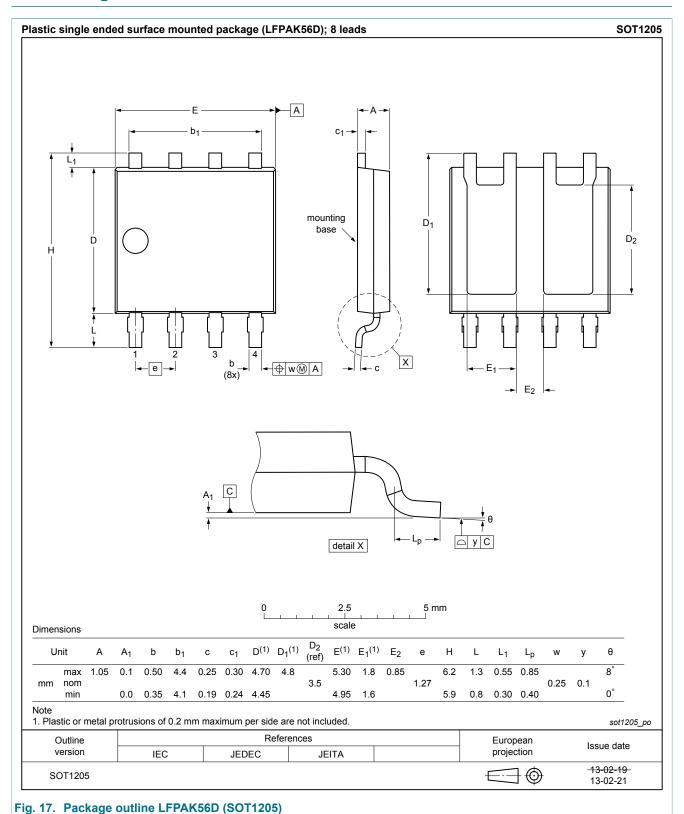


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

11. Package outline



12. Legal information

12.1 Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
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